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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/773,522	02/06/2004	Herb H. Huang	021653-000900US	6545
20350 7590 09/13/2007 TOWNSEND AND TOWNSEND AND CREW, LLP TWO EMBARCADERO CENTER EIGHTH FLOOR SAN FRANCISCO, CA 94111-3834			EXAMINER LANDAU, MATTHEW C	
			ART UNIT 2815	PAPER NUMBER
			MAIL DATE 09/13/2007	DELIVERY MODE PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary

Application No.

10/773,522

Applicant(s)

HUANG ET AL.

Examiner

Matthew C. Landau

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 14 June 2007.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-10 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-10 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f):
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- ☐ Notice of References Cited (PTO-892)
- ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- ☐ Information Disclosure Statement(s) (PTO/SB/08)
Paper No(s)/Mail Date _____
- ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
- ☐ Notice of Informal Patent Application
- ☐ Other: _____

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-4 and 6-8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shiau (US Pat. 6,372,580) in view of Yang et al. (US Pat. 6,847,087, hereinafter Yang).

Regarding claim 1, Shiau teach a method for manufacturing ROM memory devices in figure 4 and figures 5A-11 D, the method comprising:

- forming a cell region as an array region for ROM memory devices (figure 4), the array including containing continuous bit line regions BN+ in each cell (the bit lines BN+ are formed in figures 6A-6D);
- forming a gate structure POLY within the cell region (figures 9A-9D);
- forming a first sidewall spacer 47 overlying a first side of the gate structure POLY and a second sidewall spacer 47 overlying a second side of the gate structure POLY (figures 10B and 10D, column 4 lines 47-48), each sidewall spacer extends over and overlaps a portion of source/drain regions BN+ (as in the instant application, the source/drain regions are a part of the bit lines BN+), the first and second sidewall spacer 47 also adapted to separate the gate structure POLY from the source/drain regions BN+;

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- applying a refractory metal overlying the entire substrate including the gate structure POLY including the first and second sidewall spacers 47 (column 4 line 56 through column 5 line 4);

- heat treating to form silicide regions 51 overlying the gate structure POLY and exposed portions of the source/drain regions BN÷ (it is noted that Shiau does not explicitly state their heat treatment resulting in "alloying" the refractory metal; nonetheless, this is implicitly taught by Shiau as alloying is inherent in heat treating to form the silicide; that is, the silicon and the metal inherently alloy together in forming the silicide)

- and selectively removing the refractory metal layer from the sidewall spacers (figures 11A-11D and column 4 line 56 through column 5 line 4; note that the refractory metal layer is removed from 'all sections where it did not form an alloy, that is all section except for where the refractory metal contacted the polysilicon gate and silicon substrate directly).

Shiau does not teach forming a trench isolation structure within a cell region of the substrate. Since Shiau does not teach forming the isolation structure, Shiau also does not teach the claimed features and arrangement of the isolation structure and it's structural arrangement.

Yang teaches in figures 2(a)-2(c) a ROM memory array which includes continuous bit lines (SPW1/SPW2/SPW3) and gate structures (M0~M15) extending over and perpendicular to the bit lines. Yang also teaches a shallow trench isolation structure (STI) within a cell region. The shallow trench isolation structure, as seen in figures 2(b) and 2(c), are provided between adjacent bit lines extending in the same direction as the bit lines to isolate adjacent bit lines

Shiau and Yang are from the same field of endeavor. At the time of the invention, it would have been obvious to one of ordinary skill in the art to employ the trench isolation structures of Yang in the method and device of Shiau. The motivation for doing so is to isolate the bit lines from each other (Yang column 4 lines 44-47). Therefore, it would have been obvious to combine Shiau with Yang to obtain the invention of claim 1.

In combining the trench isolation regions of Yang into the method and device of Shiau, the resulting method renders claim 1 obvious. In the combination, the trench isolation structure will separate a continuous bit line region of the cell from another bit line region from another cell, the sidewall spacers will extend over and overlap a portion of the trench isolation structure, and the trench isolation structure will be separated from the gate structure by the sidewall spacers. Further, since the refractory metal layer of Shiau is applied over the entire substrate surface, it will be applied over an exposed portion of the trench isolation structure and the refractory metal will be selectively removed from the exposed surface of the trench isolation structure since it will not alloy to form the silicide on this portion:

Regarding claim 2, the refractory metal layer of Shiau is titanium or cobalt (column 4 line 56).

Regarding claim 3, the trench isolation region of Yang is an STI region (figure 2(b)).

Regarding claim 4, it is obvious to one of ordinary skill in the art at the time of the invention that the STI region comprises silicon dioxide since silicon dioxide is a commonly used material for filling trenches in STI applications.

Regarding claim 6, the first and second sidewall spacers of Shiau are a dielectric material (column 4 line 52).

Regarding claim 7, the buried bit line structure of Shiau is within the source/drain region.

Regarding claim 8, the trench isolation STI is within the substrate at a predetermined depth which is greater than a junction depth of the buried bit line SPW (Yang, column 4 lines 48-51).

Claims 5 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shiau with Yang as applied to claims 1-4 and 6-8 above, and further in view of Iwata et al. (US 2004/0262650 A1).

Liu with Shiau do not explicitly disclose a channel region using a length of about 0.25 micron and less or the gate structure having a width of 0.25 micron and less. Iwata et al. teach semiconductor devices. Iwata et al. teach in paragraph 3 that recently the integration level of semiconductor devices is becoming higher and higher and thus there is a demand for smaller elements. Iwata et al. teach in paragraph 24 that the gate electrode (gate structure) is formed to a width of 100 nm (0.1 micron). It is noted that this paragraph relates to figure 44, which shows that channel length as the same as the gate width, thus Iwata teach both the gate structure and channel length of less than 0.25 micron.

Shiau with Yang and Iwata et al. are combinable because they are from the same field of endeavor. At the time of the invention it would have been obvious to one of ordinary skill in the art to form the gate structure width and channel length to 0.25 micron or less. The motivation for doing so is to meet the demand for smaller elements for higher integration. Therefore, it would

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have been obvious to combine Shiau and Yang with Iwata et al. to obtain the invention of claims 5 and 9.

Claim 10 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shiau with Yang as applied to claims 1-4 and 6-8 above, and further in view of Chang (US Patent No. 5,506,160).

Shiau and Yang each teach an array of ROM cells (see figure 3A of Liu and figure 4 of Shiau, for example) but do not explicitly disclose their array having at least eight cells by eight cells. Nonetheless, it is considered obvious to form a ROM array to have at least eight cells by eight cells. Each cell represents one bit of data. Chang teach a ROM array in figure 5, for example. Chang et al. teach forming the array to be a 64 Mbit array. As one of ordinary skill in the art would recognize, a 64 Mbit array has at least eight cells by eight cells. At the time of the invention, it would have been obvious to one of ordinary skill in the art to form the array of Shiau with Yang to have at least eight cells by eight cells. The motivation for doing so is to meet an industry need of higher integration and larger memory arrays and to provide a greater amount of memory needed for modern electronics devices. Thus, it would have been obvious to form the array to at least eight cells by eight cells as claimed.

Response to Arguments

Applicant's arguments filed June 14, 2007 have been fully considered but they are not persuasive.

Applicant argues that “there is absolutely no motivation in the Shiau Patent that would motivate one of ordinary skill in the art to combine it with the Yang Patent”. However, there is no requirement that the motivation for combining references must come from the primary reference. In the above rejection, the Examiner clearly provided a motivation for combining the references, and that motivation came directly from the secondary reference (Yang). Applicant further argues that because Yang uses a contact plug which penetrates the surface of the drain region and buried bit lines, “use of the silicide process and the formation of a silicide layer as taught in the Shiau Patent, in combination with the Yang Patent, would be nonsensical since the silicide layer of the Shiau Patent is used to decrease the electric resistance of the drain and bit line region, while the contact plug of the Yang patent is electrically coupled to short-circuit this region”. This argument is not persuasive since at no point did the above rejection suggest incorporating the silicide process of Shiau into the device of Yang. As clearly stated above, the point to the rejection was to use the STI isolation of Yang in the device of Shiau. Whether or not the silicide of Shiau can be used in the device of Yang is irrelevant since such a combination was not proposed. It should be noted that the test for obviousness is not whether the features of a secondary reference may be bodily incorporated into the structure of the primary reference; nor is it that the claimed invention must be expressly suggested in any one or all of the references. Rather, the test is what the combined teachings of the references would have suggested to those of ordinary skill in the art. See *In re Keller*, 642 F.2d 413, 208 USPQ 871 (CCPA 1981).

Conclusion

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

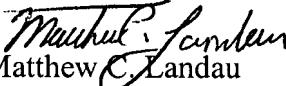
A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Matthew C. Landau whose telephone number is 571-272-1731. The examiner can normally be reached on 9:00AM - 5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Ken Parker can be reached on 571-272-2298. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.


Matthew C. Landau
Primary Examiner
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9/5/07